

134. (New) A method for making a thin film semi-conductor comprising the steps of:

forming a first porous layer having a first porosity on a surface of a substrate;

forming a second porous layer within or underneath said first porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers,

wherein said first porous layer and said second porous layer are formed by anodizing.

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forming a first porous layer having a first porosity on a surface of a substrate;

forming a second porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers,

wherein said first porous layer and said second porous layer are formed by anodizing.

136. (New) A method for making a thin film semi-conductor comprising the steps of:

forming a first porous layer having a first porosity on a surface of a substrate;

forming a second porous layer within or underneath said first porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semiconductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers

137. (New) A thin film semi-conductor formed by:

providing a semi-conductor substrate having a surface;

forming a first porous layer having a first porosity on a surface of said substrate;

forming a second porous layer within or underneath said first porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers to obtain said thin film semi-conductor,

wherein said first porous layer and said second porous layer are formed by anodizing.

138. (New) A thin film semi-conductor formed by:
providing a semi-conductor substrate having a surface;
forming a first porous layer having a first porosity on a surface of said substrate;
forming a second porous layer having a second porosity higher than said first porosity;
forming at least one semi-conductor thin film on said surface; and
separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers to obtain said thin film semi-conductor,
wherein said first porous layer and said second porous layer are formed by anodizing.

139. (New) A thin film semi-conductor formed by:
providing a semi-conductor substrate having a surface;

forming a first porous layer having a first porosity on a surface of said substrate;

forming a second porous layer within or underneath said first porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers to obtain said thin film semiconductor.

140. (New) A thin film semi-conductor formed by:

providing a semi-conductor having a surface;

anodizing said semi-conductor substrate at a first current density to provide a first porous layer adjacent said surface having a first porosity;

anodizing said semi-conductor substrate at a second current density higher than said first current density to provide a second porous layer adjacent said first porous layer opposite said surface, said second porous layer having a second porosity greater than said first porosity;

annealing said semi-conductor substrate in a hydrogen atmosphere after said step of anodizing said semi-conductor substrate to provide said second porous layer; and

forming at least one semi-conductor film on said surface.

141. (New) A thin film semi-conductor formed by:
providing a semi-conductor having a surface;
anodizing said semi-conductor substrate at a first current density to provide
a first porous layer adjacent said surface having a first porosity;
anodizing said semi-conductor substrate at a second current density higher
than said first current density to provide a second porous layer adjacent said first porous
layer opposite said surface, said second porous layer having a second porosity greater than
said first porosity;
forming at least one semi-conductor film on said surface.

142. (New) A thin film semi-conductor formed by:
providing a semi-conductor substrate having a surface;
forming a first porous layer adjacent said surface having a first porosity;
forming a second porous layer within said first porous layer having a second
porosity higher than said first porosity;
forming at least one semi-conductor film on said surface; and
separating said semi-conductor film from said semi-conductor substrate
along a line of relative weakness defined in or adjacent one of said first and second porous
layers.
